

Abstract

A plasma etching equipment (5) is proposed for especially anisotropic etching a substrate (13) by the action of a plasma (21). For this purpose, a first, especially inductively coupled plasma-generating device (31) is provided, which has a first means (11) for generating a first high-frequency electromagnetic alternating field, an etching chamber (10) for generating a first plasma (21) from reactive particles by the action of the first high-frequency electromagnetic alternating field upon a first reactive gas with the substrate (13) to be etched, and a first gas supply (22). A second plasma-generating device (32) is preconnected to this first plasma-generating device (31), and it has a second means (20), especially a microwave generator (20), for generating a second high-frequency electromagnetic alternating field, a plasma-generating region (33) for generating a second plasma (18) from reactive particles by the action of the second high-frequency electromagnetic alternating field upon a second reactive gas, and a second gas supply (16). In this connection, the generated second plasma (18) of the first plasma-generating device (31) can be supplied at least partially as first reactive gas via the first gas supply (32).

(Figure)